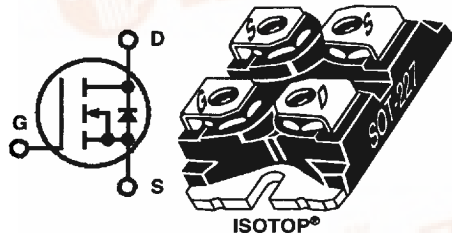


查询APT10026JNR供应商

捷多邦, 专业PCB打样工厂, 24小时加急

出货



**ADVANCED
POWER
TECHNOLOGY®**
APT10026JNR 1000V 33A 0.26Ω

UL Recognized" File No. E145592 (S)

POWER MOS IV®

AVALANCHE RATED ISOTOP® PACKAGE

N-CHANNEL ENHANCEMENT MODE LOW VOLTAGE POWER MOSFETS

MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Parameter	APT10026JNR	UNIT
V_{DS}	Drain-Source Voltage	1000	Volts
I_D	Continuous Drain Current @ $T_C = 25^\circ\text{C}$	33	Amps
I_{DM}	Pulsed Drain Current ①	132	
V_{GS}	Gate-Source Voltage Continuous	± 20	Volts
V_{GSM}	Gate-Source Voltage Transient	± 30	
P_D	Total Power Dissipation @ $T_C = 25^\circ\text{C}$	690	Watts
	Linear Derating Factor	5.52	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150	$^\circ\text{C}$
T_L	Lead Temperature: 0.063" from Case for 10 Sec.	300	
I_{AR}	Avalanche Current ① (Repetitive and Non-Repetitive)	33	Amps
E_{AR}	Repetitive Avalanche Energy ①	30	mJ
E_{AS}	Single Pulse Avalanche Energy ④	3600	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions / Part Number	MIN	TYP	MAX	UNIT
BV_{DS}	Drain-Source Breakdown Voltage ($V_{GS} = 0V, I_D = 250\mu A$)	1000			Volts
$I_{D(ON)}$	On State Drain Current ②	APT10026JNR	33		Amps
	($V_{DS} > I_{D(ON)} \times R_{DS(ON)}$ Max, $V_{GS} = 10V$)				
$R_{DS(ON)}$	Drain-Source On-State Resistance ②	APT10026JNR		0.26	Ohms
	($V_{GS} = 10V, 0.5 I_D$ [Cont.])				
I_{DSS}	Zero Gate Voltage Drain Current ($V_{DS} = 0.8 V_{DSS}, V_{GS} = 0V$)			250	μA
	Zero Gate Voltage Drain Current ($V_{DS} = 0.8 V_{DSS}, V_{GS} = 0V, T_C = 125^\circ\text{C}$)			1000	
I_{GSS}	Gate-Source Leakage Current ($V_{GS} = \pm 20V, V_{DS} = 0V$)			± 100	nA
$V_{GS(TH)}$	Gate Threshold Voltage ($V_{DS} = V_{GS}, I_D = 5.0mA$)	2		4	Volts

THERMAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case			0.18	$^\circ\text{C/W}$
$R_{\theta CS}$	Case to Sink (Use High Efficiency Thermal Joint Compound and Planar Heat Sink Surface.)		0.08		

CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

USA

405 S.W. Columbia Street

EUROPE

Avenue J.F. Kennedy Bât B4 Parc Cadéra Nord F-33700 Merignac - France

Bend, Oregon 97702-1035

Phone: (541) 382-8028 FAX: (541) 388-0364

Phone: (33) 57 92 15 15 FAX: (33) 56 47 97 61

050-0055 Rev A



DYNAMIC CHARACTERISTICS

APT10026JNR

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C_{iss}	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1\text{ MHz}$		20000	24000	pF
C_{oss}	Output Capacitance			1600	2240	
C_{rss}	Reverse Transfer Capacitance			500	750	
Q_g	Total Gate Charge ③	$V_{GS} = 10V$ $V_{DD} = 0.5 V_{DSS}$ $I_D = I_D [\text{Cont.}] @ 25^\circ\text{C}$		650	975	nC
Q_{gs}	Gate-Source Charge			70	105	
Q_{gd}	Gate-Drain ("Miller") Charge			250	375	
$t_{d(on)}$	Turn-on Delay Time	$V_{GS} = 15V$ $V_{DD} = 0.5 V_{DSS}$ $I_D = I_D [\text{Cont.}] @ 25^\circ\text{C}$ $R_G = 0.6\Omega$		25	38	ns
t_r	Rise Time			20	30	
$t_{d(off)}$	Turn-off Delay Time			110	220	
t_f	Fall Time			20	40	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Symbol	Characteristic / Test Conditions / Part Number	MIN	TYP	MAX	UNIT
I_S	Continuous Source Current (Body Diode)	APT10026JNR		33	Amps
I_{SM}	Pulsed Source Current ① (Body Diode)	APT10026JNR		132	
V_{SD}	Diode Forward Voltage ② ($V_{GS} = 0V$, $I_S = -I_D [\text{Cont.}]$)			1.3	Volts
t_{rr}	Reverse Recovery Time ($I_S = -I_D [\text{Cont.}]$, $dI_S/dt = 100A/\mu s$)		1300	2600	ns
Q_{rr}	Reverse Recovery Charge ($I_S = -I_D [\text{Cont.}]$, $dI_S/dt = 100A/\mu s$)		29	58	μC

PACKAGE CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
L_D	Internal Drain Inductance (Measured From Drain Terminal to Center of Die.)		3		nH
L_S	Internal Source Inductance (Measured From Source Terminals to Source Bond Pads)		5		
$V_{isolation}$	RMS Voltage (50-60 Hz Sinusoidal Waveform From Terminals to Mounting Base for 1 Min.)	2500			Volts
$C_{isolation}$	Drain-to-Mounting Base Capacitance ($f = 1\text{MHz}$)		38		pF
Torque	Maximum Torque for Device Mounting Screws and Electrical Terminations.			13	lb•in.

① Repetitive Rating: Pulse width limited by maximum junction temperature.

③ See MIL-STD-750 Method 3471

② Pulse Test: Pulse width < 380 μs , Duty Cycle < 2%

④ Starting $T_j = 25^\circ\text{C}$, $L = 6.6\text{mH}$, $R_G = 25\Omega$, Peak $I_L = 33A$

APT Reserves the right to change, without notice, the specifications and information contained herein.

SOT-227 (ISOTOP®) Package Outline

